Global Communication Semiconductors, LLC
Corporate & Foundry
23155 Kashiwa Court, Torrance, CA. 90505
Telephone: 310-530-7274 Fax: 310-517-8200
Website: www.gcsincorp.com

Process Integration Engineer

1. Responsible for process integration/device engineering in SiC technology and devices, specializing in process optimization, characterization and integration for such devices.

2. Perform various materials and electrical characterizations on SiC semiconductor devices for solving process integration issues in a semiconductor fabrication line.

3. Responsible for the sustaining optimization and improvement of SiC semiconductor manufacturing steps both individually and collectively.

4. Interact with customers and other process engineers at the technical level to define and optimize device parameters and process flows, and to assist in the reduction of production costs.

5. Develop the manufacturing process of InP High Electron Mobility Transistor (HEMT), determine key process parameters and transfer the technology from R&D mode to production mode.

6. Conduct device characterization, process qualification and yield improvement of pHEMT, HFET and MESFET production.

Require Bachelor’s degree in Electrical Engineering, Materials Science or Engineering, or a related field.

Requires two years’ experience in job offered or in R&D of compound semiconductor device. Requires experience in compound semiconductor device process development, device testing, dry and wet etch, photolithography, PVD and CVD, SEM and failure analysis.

Location: Torrance, CA

CONTACT: hr@gcsincorp.com
Human Resources
23155 Kashiwa Court
Torrance, CA 90505